# 74HC164; 74HCT164

# 8-bit serial-in, parallel-out shift register Rev. 04 — 2 February 2010

**Product data sheet** 

### 1. **General description**

The 74HC164; 74HCT164 are high-speed Si-gate CMOS devices and are pin compatible with Low power Schottky TTL (LSTTL). They are specified in compliance with JEDEC standard no. 7A.

The 74HC164; 74HCT164 are 8-bit edge-triggered shift registers with serial data entry and an output from each of the eight stages. Data is entered serially through one of two inputs (DSA or DSB); either input can be used as an active HIGH enable for data entry through the other input. Both inputs must be connected together or an unused input must be tied HIGH.

Data shifts one place to the right on each LOW-to-HIGH transition of the clock (CP) input and enters into Q0, which is the logical AND of the two data inputs (DSA and DSB) that existed one set-up time prior to the rising clock edge.

A LOW level on the master reset  $(\overline{MR})$  input overrides all other inputs and clears the register asynchronously, forcing all outputs LOW.

### **Features**

- Input levels:
  - For 74HC164: CMOS level
  - For 74HCT164: TTL level
- Gated serial data inputs
- Asynchronous master reset
- Complies with JEDEC standard no. 7A
- ESD protection:
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V.
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C.

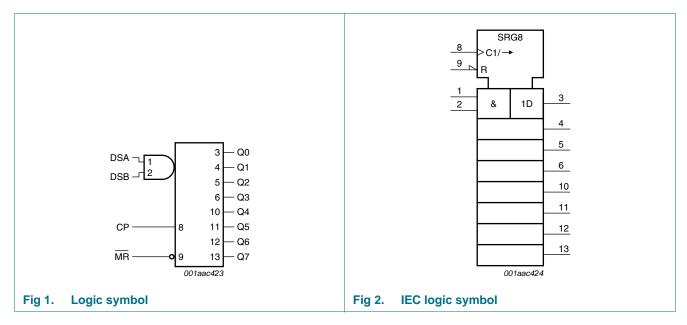


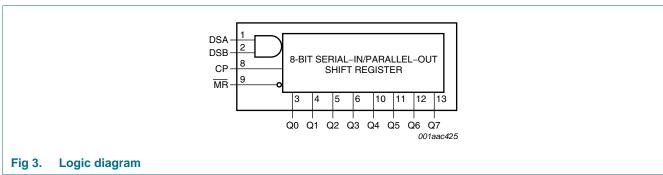
# 3. Ordering information

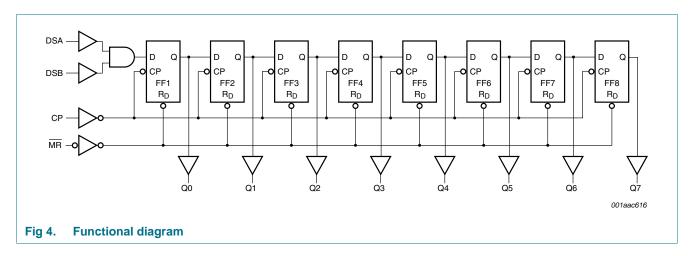
Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC164N	–40 °C to +125 °C	DIP14	plastic dual in-line package; 14 leads (300 mil)	SOT27-1
74HCT164N				
74HC164D	–40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width	SOT108-1
74HCT164D			3.9 mm	
74HC164DB	–40 °C to +125 °C	SSOP14	plastic shrink small outline package; 14 leads; body	SOT337-1
74HCT164DB			width 5.3 mm	
74HC164PW	–40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads;	SOT402-1
74HCT164PW			body width 4.4 mm	
74HC164BQ	–40 °C to +125 °C	DHVQFN14	plastic dual in-line compatible thermal enhanced very	SOT762-1
74HCT164BQ	_		thin quad flat package; no leads; 14 terminals; body $2.5 \times 3 \times 0.85$ mm	

# 4. Functional diagram

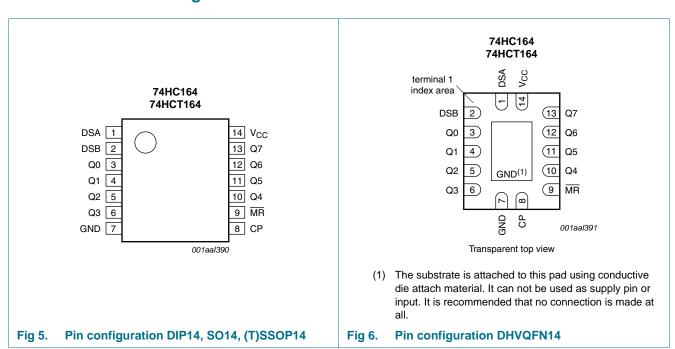






# 5. Pinning information

## 5.1 Pinning



# 5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
DSA	1	data input
DSB	2	data input
Q0 to Q7	3, 4, 5, 6, 10, 11, 12, 13	output
GND	7	ground (0 V)
СР	8	clock input (LOW-to-HIGH, edge-triggered)
MR	9	master reset input (active LOW)
V <sub>CC</sub>	14	positive supply voltage

# 6. Functional description

Table 3. Function table[1]

Operating	Input		Output	Output		
modes	MR	СР	DSA	DSB	Q0	Q1 to Q7
Reset (clear)	L	X	X	X	L	L to L
Shift	Н	<b>↑</b>	I	I	L	q0 to q6
	Н	<b>↑</b>	I	h	L	q0 to q6
	Н	<b>↑</b>	h	I	L	q0 to q6
	Н	<b>↑</b>	h	h	Н	q0 to q6

<sup>[1]</sup> H = HIGH voltage level

h = HIGH voltage level one set-up time prior to the LOW-to-HIGH clock transition

# 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+7	V
I <sub>IK</sub>	input clamping current	$V_I < -0.5 \text{ V or } V_I > V_{CC} + 0.5 \text{ V}$	<u>[1]</u> _	±20	mA
I <sub>OK</sub>	output clamping current	$V_O < -0.5 \text{ V or } V_O > V_{CC} + 0.5 \text{ V}$	<u>[1]</u> _	±20	mA
Io	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±25	mA
I <sub>CC</sub>	supply current		-	50	mA
I <sub>GND</sub>	ground current		-50	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C

L = LOW voltage level

I = LOW voltage level one set-up time prior to the LOW-to-HIGH clock transition

q = lower case letters indicate the state of the referenced input one set-up time prior to the LOW-to-HIGH clock transition

<sup>↑ =</sup> LOW-to-HIGH clock transition

Table 4. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
P <sub>tot</sub>	total power dissipation		[2]		
	DIP14 package		-	750	mW
	SO14, (T)SSOP14 and DHVQFN14 packages		-	500	mW

<sup>[1]</sup> The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

For SO14 package:  $P_{tot}$  derates linearly with 8 mW/K above 70 °C.

For (T)SSOP14 packages: Ptot derates linearly with 5.5 mW/K above 60 °C.

For DHVQFN14 packages: Ptot derates linearly with 4.5 mW/K above 60 °C.

# 8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	74HC1	64		74HC1	74HCT164			
			Min	Тур	Max	Min	Тур	Max		
$V_{CC}$	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V	
$V_{I}$	input voltage		0	-	$V_{CC}$	0	-	$V_{CC}$	V	
Vo	output voltage		0	-	$V_{CC}$	0	-	$V_{CC}$	V	
$T_{amb}$	ambient temperature		-40	+25	+125	-40	+25	+125	°C	
Δt/ΔV	input transition rise and fall rate	$V_{CC} = 2.0 \text{ V}$	-	-	625	-	-	-	ns/V	
		$V_{CC} = 4.5 \text{ V}$	-	1.67	139	-	1.67	139	ns/V	
		$V_{CC} = 6.0 \text{ V}$	-	-	83	-	-	-	ns/V	

## 9. Static characteristics

### Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbo	I Parameter	Conditions		25 °C			o +85 °C	–40 °C to	Unit	
			Min	Тур	Max	Min	Max	Min	Max	
74HC16	64						•			
$V_{IH}$	HIGH-level	$V_{CC} = 2.0 \text{ V}$	1.5	1.2	-	1.5	-	1.5	-	V
	input voltage	V <sub>CC</sub> = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V <sub>CC</sub> = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
$V_{IL}$	LOW-level	$V_{CC} = 2.0 \text{ V}$	-	8.0	0.5	-	0.5	-	0.5	V
	input voltage	$V_{CC} = 4.5 \text{ V}$	-	2.1	1.35	-	1.35	-	1.35	V
		V <sub>CC</sub> = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V

<sup>[2]</sup> For DIP14 package:  $P_{tot}$  derates linearly with 12 mW/K above 70 °C.

**Table 6.** Static characteristics ...continued
At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C t	:o +85 °C	-40 °C to	Unit	
			Min	Тур	Max	Min	Max	Min	Max	
V <sub>OH</sub>	HIGH-level	$V_I = V_{IH}$ or $V_{IL}$					'			
	output voltage	$I_O = -20 \mu A$ ; $V_{CC} = 2.0 \text{ V}$	1.9	2.0	-	1.9	-	1.9	-	V
		$I_O = -20 \mu A; V_{CC} = 4.5 V$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_O = -20 \mu A; V_{CC} = 6.0 V$	5.9	6.0	-	5.9	-	5.9	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.98	4.32	-	3.84	-	3.7	-	V
		$I_{O} = -5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.48	5.81	-	5.34	-	5.2	-	V
$V_{OL}$	LOW-level	$V_I = V_{IH}$ or $V_{IL}$								
	output voltage	$I_O = 20 \mu A; V_{CC} = 2.0 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 6.0 \text{ V}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 4.0 \text{ mA}$ ; $V_{CC} = 4.5 \text{ V}$	-	0.15	0.26	-	0.33	-	0.4	V
		$I_{O} = 5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.26	-	0.33	-	0.4	V
I <sub>I</sub>	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	±0.1	-	±1	-	±1	μΑ
I <sub>CC</sub>	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0 \text{ V}$	-	-	8.0	-	80	-	160	μΑ
C <sub>I</sub>	input capacitance		-	3.5	-	-	-	-	-	pF
74HCT1	64									
V <sub>IH</sub>	HIGH-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	2.0	1.6	-	2.0	-	2.0	-	V
$V_{IL}$	LOW-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	1.2	8.0	-	8.0	-	8.0	V
V <sub>OH</sub>	HIGH-level	$V_I = V_{IH}$ or $V_{IL}$ ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	$I_{O} = -20 \mu A$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -4.0 \text{ mA}$	3.98	4.32	-	3.84	-	3.7	-	V
$V_{OL}$	LOW-level	$V_I = V_{IH}$ or $V_{IL}$ ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	$I_O = 20 \mu A$ ; $V_{CC} = 4.5 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.15	0.26	-	0.33	-	0.4	V
I <sub>I</sub>	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	±0.1	-	±1	-	±1	μΑ
I <sub>CC</sub>	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0 \text{ V}$	-	-	8	-	80	-	160	μΑ
Δl <sub>CC</sub>	additional supply current	per input pin; $V_I = V_{CC} - 2.1 \text{ V}; I_O = 0 \text{ A};$ other inputs at $V_{CC}$ or GND; $V_{CC} = 4.5 \text{ V}$ to 5.5 V	-	100	360	-	450	-	490	μА
Cı	input capacitance		-	3.5	-	-	-	-	-	pF

# 10. Dynamic characteristics

Table 7. Dynamic characteristics

GND = 0 V;  $t_r = t_f = 6 \text{ ns}$ ;  $C_L = 50 \text{ pF}$ ; test circuit see Figure 10; unless otherwise specified

Symbol	Parameter	Conditions			25 °C		-40 °C t	o +85 °C	-40 °C to	o +125 °C	Unit
				Min	Тур	Max	Min	Max	Min	Max	
74HC164	ı			ı			ı			'	
t <sub>pd</sub>	propagation	CP to Qn; see Figure 7	[1]								
	delay	$V_{CC} = 2.0 \text{ V}$		-	41	170	-	215	-	255	ns
		$V_{CC} = 4.5 \text{ V}$		-	15	34	-	43	-	51	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	12	-	-	-	-	-	ns
		$V_{CC} = 6.0 \text{ V}$		-	12	29	-	37	-	43	ns
t <sub>PHL</sub>	HIGH to LOW	MR to Qn; see Figure 8									
	propagation	$V_{CC} = 2.0 \text{ V}$		-	39	140	-	175	-	210	ns
	delay	$V_{CC} = 4.5 \text{ V}$		-	14	28	-	35	-	42	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	11	-	-	-	-	-	ns
		$V_{CC} = 6.0 \text{ V}$		-	11	24	-	30	-	36	ns
t <sub>t</sub>	transition time	see Figure 7	[2]								
		$V_{CC} = 2.0 \text{ V}$		-	19	75	-	95	-	110	ns
		$V_{CC} = 4.5 \text{ V}$		-	7	15	-	19	-	22	ns
		$V_{CC} = 6.0 \text{ V}$		-	6	13	-	16	-	19	ns
$t_{W}$	pulse width	CP HIGH or LOW; see Figure 7									
		$V_{CC} = 2.0 \text{ V}$		80	14	-	100	-	120	-	ns
		$V_{CC} = 4.5 \text{ V}$		16	5	-	20	-	24	-	ns
		$V_{CC} = 6.0 \text{ V}$		14	4	-	17	-	20	-	ns
		MR LOW; see Figure 8									
		$V_{CC} = 2.0 \text{ V}$		60	17	-	75	-	90	-	ns
		$V_{CC} = 4.5 \text{ V}$		12	6	-	15	-	18	-	ns
		$V_{CC} = 6.0 \text{ V}$		10	5	-	13	-	15	-	ns
t <sub>rec</sub>	recovery time	MR to CP; see Figure 8									
		$V_{CC} = 2.0 \text{ V}$		60	17	-	75	-	90	-	ns
		$V_{CC} = 4.5 \text{ V}$		12	6	-	15	-	18	-	ns
		$V_{CC} = 6.0 \text{ V}$		10	5	-	13	-	15	-	ns
t <sub>su</sub>	set-up time	DSA, and DSB to CP; see Figure 9									
		V <sub>CC</sub> = 2.0 V		60	8	-	75	-	90	-	ns
		$V_{CC} = 4.5 \text{ V}$		12	3	-	15	-	18	-	ns
		$V_{CC} = 6.0 \text{ V}$		10	2	-	13	-	15	-	ns
t <sub>h</sub>	hold time	DSA, and DSB to CP; see Figure 9									
		V <sub>CC</sub> = 2.0 V		+4	-6	-	4	-	4	-	ns
		$V_{CC} = 4.5 \text{ V}$		+4	-2	-	4	-	4	-	ns
		V <sub>CC</sub> = 6.0 V		+4	-2	-	4	_	4		ns

Table 7. Dynamic characteristics

 $GND = 0 \ V; \ t_r = t_f = 6 \ ns; \ C_L = 50 \ pF; \ test \ circuit \ see \ Figure 10; \ unless \ otherwise \ specified$ 

Symbol	Parameter	Conditions			25 °C		-40 °C t	o +85 °C	–40 °C to	+125 °C	Unit
				Min	Тур	Max	Min	Max	Min	Max	
f <sub>max</sub>	maximum	for Cp, see Figure 7					1		ı		
	frequency	$V_{CC} = 2.0 \text{ V}$		6	23	-	5	-	4	-	MHz
		$V_{CC} = 4.5 \text{ V}$		30	71	-	24	-	20	-	MHz
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	78	-	-	-	-	-	MHz
		$V_{CC} = 6.0 \text{ V}$		35	85	-	28	-	24	-	MHz
C <sub>PD</sub>	power dissipation capacitance	per package; V <sub>I</sub> = GND to V <sub>CC</sub>	[3]	-	40	-	-	-	-	-	pF
74HCT1	64										
t <sub>pd</sub>	propagation	CP to Qn; see Figure 7	[1]								
	delay	$V_{CC} = 4.5 \text{ V}$		-	17	36	-	45	-	54	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	14	-	-	-	-	-	ns
t <sub>PHL</sub>	HIGH to LOW	MR to Qn; see Figure 8									
	propagation delay	$V_{CC} = 4.5 \text{ V}$		-	19	38	-	48	-	57	ns
	uelay	$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	16	-	-	-	-	-	ns
t <sub>t</sub>	transition time	see Figure 7	[2]								
		$V_{CC} = 4.5 V$		-	7	15	-	19	-	22	ns
$t_W$	pulse width	CP HIGH or LOW; see Figure 7									
		$V_{CC} = 4.5 \text{ V}$		18	7	-	23	-	27	-	ns
		MR LOW; see Figure 8									
		$V_{CC} = 4.5 \text{ V}$		18	10	-	23	-	27	-	ns
t <sub>rec</sub>	recovery time	MR to CP; see Figure 8									
		$V_{CC} = 4.5 \text{ V}$		16	7	-	20	-	24	-	ns
t <sub>su</sub>	set-up time	DSA, and DSB to CP; see Figure 9									
		$V_{CC} = 4.5 \text{ V}$		12	6	-	15	-	18	-	ns
t <sub>h</sub>	hold time	DSA, and DSB to CP; see Figure 9									
		$V_{CC} = 4.5 \text{ V}$		+4	-2	-	4	-	4	-	ns
f <sub>max</sub>	maximum	for Cp, see Figure 7									
	frequency	$V_{CC} = 4.5 V$		27	55	-	22	-	18	-	MHz
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	61	-	-	-	-	-	MHz

Table 7. Dynamic characteristics

GND = 0 V;  $t_r = t_f = 6$  ns;  $C_L = 50$  pF; test circuit see Figure 10; unless otherwise specified

Symbol	Parameter	Conditions	25 °C		-40 °C to +85 °C		-40 °C to +125 °C		Unit		
			М	lin	Тур	Max	Min	Max	Min	Max	
$C_{PD}$	power dissipation capacitance	per package; I V <sub>I</sub> = GND to V <sub>CC</sub> – 1.5 V	<u>3]</u>	-	40	-	-	-	-	-	pF

- [1]  $t_{pd}$  is the same as  $t_{PHL}$  and  $t_{PLH}$ .
- [2]  $t_t$  is the same as  $t_{THL}$  and  $t_{TLH}$ .
- [3]  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu W$ ):

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o)$$
 where:

f<sub>i</sub> = input frequency in MHz;

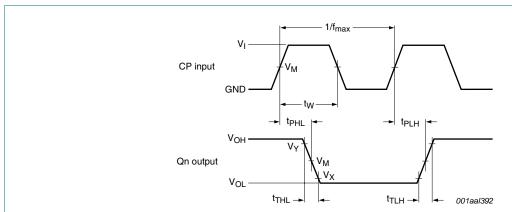
f<sub>o</sub> = output frequency in MHz;

C<sub>L</sub> = output load capacitance in pF;

V<sub>CC</sub> = supply voltage in V;

N = number of inputs switching;

 $\sum (C_L \times V_{CC}^2 \times f_o)$  = sum of outputs.



(1) Measurement points are given in Table 8.

 $V_{OL}$  and  $V_{OH}$  are typical voltage output levels that occur with the output load.

Fig 7. Waveforms showing the clock (CP) to output (Qn) propagation delays, the clock pulse width, the output transition times and the maximum clock frequency

Table 8. Measurement points

Туре	Input	Output		
	V <sub>M</sub>	V <sub>M</sub>	V <sub>X</sub>	V <sub>Y</sub>
74HC164	0.5V <sub>CC</sub>	0.5V <sub>CC</sub>	0.1V <sub>CC</sub>	0.9V <sub>CC</sub>
74HCT164	1.3 V	1.3 V	0.1V <sub>CC</sub>	0.9V <sub>CC</sub>

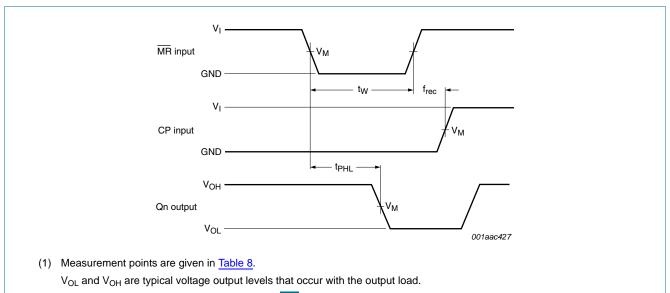
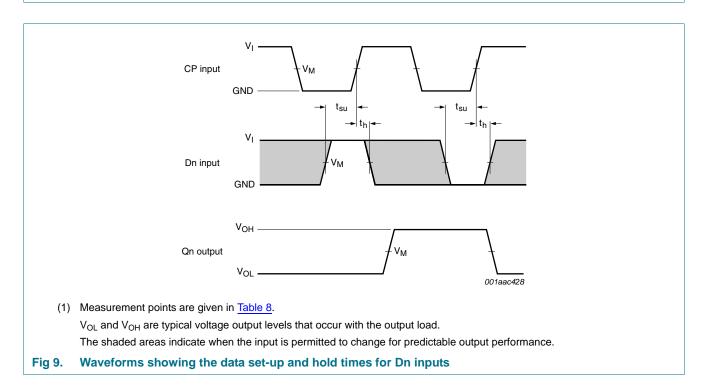
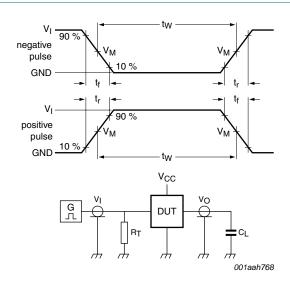


Fig 8. Waveforms showing the master reset (MR) pulse width, the master reset to output (Qn) propagation delays and the master reset to clock (CP) removal time





Test data is given in Table 9.

Definitions test circuit:

 $R_T$  = termination resistance should be equal to output impedance  $Z_0$  of the pulse generator.

 $C_L$  = load capacitance including jig and probe capacitance.

Fig 10. Test circuit for measuring switching times

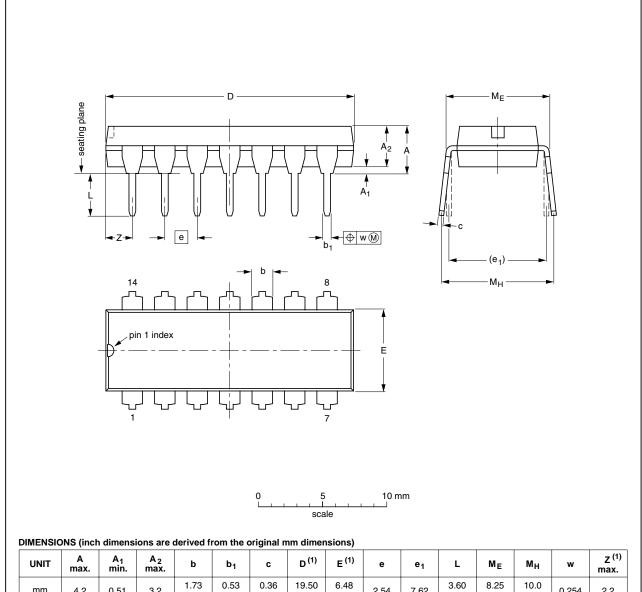
Table 9. Test data

Туре	Input		Load	Test
	VI	t <sub>r</sub> , t <sub>f</sub>	CL	
74HC164	V <sub>CC</sub>	6.0 ns	15 pF, 50 pF	t <sub>PLH</sub> , t <sub>PHL</sub>
74HCT164	3.0 V	6.0 ns	15 pF, 50 pF	t <sub>PLH</sub> , t <sub>PHL</sub>

# 11. Package outline

DIP14: plastic dual in-line package; 14 leads (300 mil)

SOT27-1



UNIT	A max.	A <sub>1</sub> min.	A <sub>2</sub> max.	b	b <sub>1</sub>	С	D <sup>(1)</sup>	E (1)	e	e <sub>1</sub>	L	ME	Мн	w	Z <sup>(1)</sup> max.
mm	4.2	0.51	3.2	1.73 1.13	0.53 0.38	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	2.2
inches	0.17	0.02	0.13	0.068 0.044	0.021 0.015	0.014 0.009	0.77 0.73	0.26 0.24	0.1	0.3	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.087

### Note

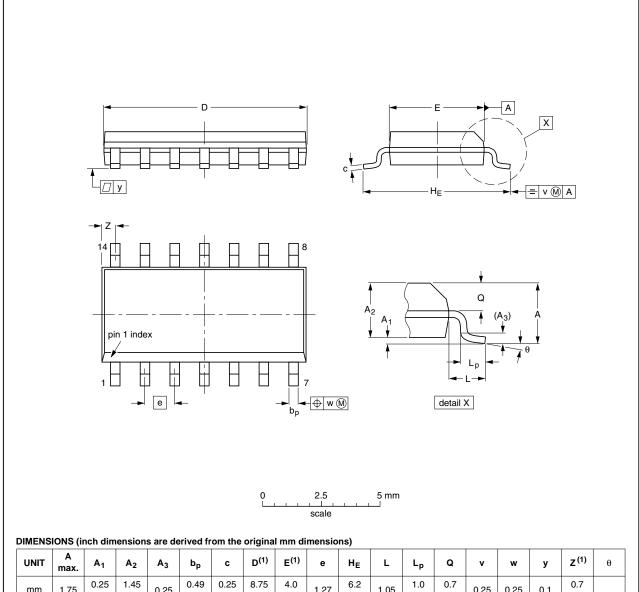
1. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT27-1	050G04	MO-001	SC-501-14		<del>99-12-27</del> 03-02-13

Fig 11. Package outline SOT27-1 (DIP14)

SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1



UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	bp	С	D <sup>(1)</sup>	E <sup>(1)</sup>	е	HE	L	Lp	Q	v	w	у	z <sup>(1)</sup>	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	8.75 8.55	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	0.069	0.010 0.004	0.057 0.049	0.01	1	0.0100 0.0075	0.35 0.34	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	0°

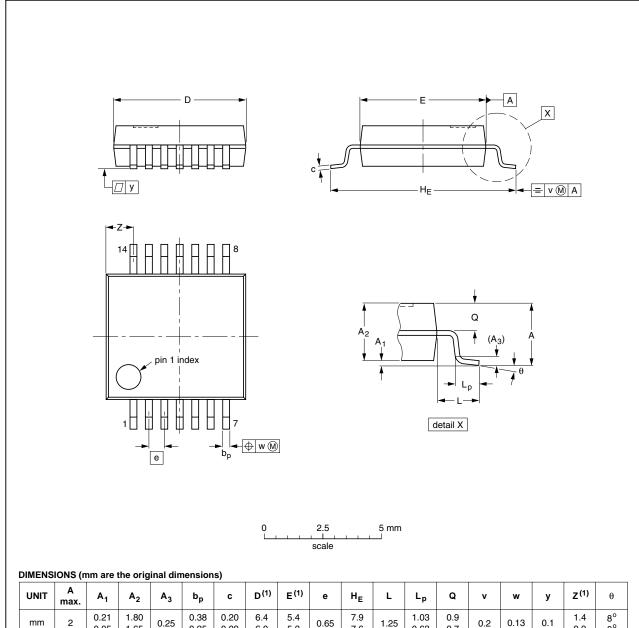
1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT108-1	076E06	MS-012				<del>99-12-27</del> 03-02-19

Fig 12. Package outline SOT108-1 (SO14)

SSOP14: plastic shrink small outline package; 14 leads; body width 5.3 mm

SOT337-1



UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	b <sub>p</sub>	ပ	D <sup>(1)</sup>	E <sup>(1)</sup>	е	HE	L	Lp	Q	v	w	у	Z <sup>(1)</sup>	θ
mm	2	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	6.4 6.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	1.4 0.9	8° 0°

### Note

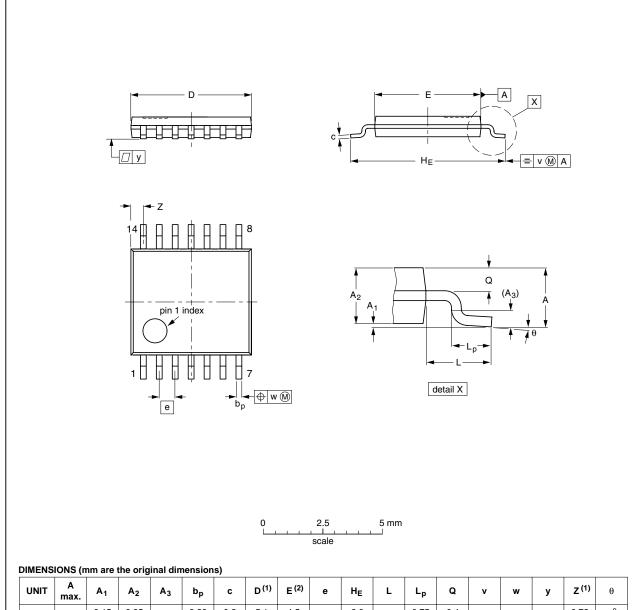
1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT337-1		MO-150			<del>99-12-27</del> 03-02-19

Fig 13. Package outline SOT337-1 (SSOP14)

TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1



UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	bp	С	D <sup>(1)</sup>	E (2)	е	HE	L	Lp	Ø	v	w	у	Z <sup>(1)</sup>	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.72 0.38	8° 0°

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT402-1		MO-153				<del>99-12-27</del> 03-02-18
	•	•				

Fig 14. Package outline SOT402-1 (TSSOP14)

DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 x 3 x 0.85 mm SOT762-1

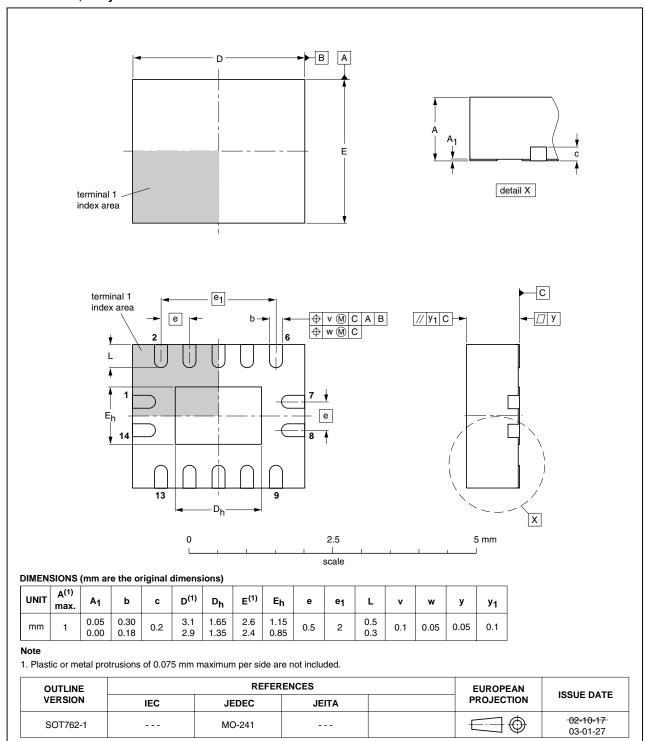


Fig 15. Package outline SOT762-1 (DHVQFN14)

# 12. Abbreviations

### Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
LSTTL	Low-power Schottky Transistor-Transistor Logic
MM	Machine Model
TTL	Transistor-Transistor Logic

# 13. Revision history

### Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT164_4	20100202	Product data sheet	-	74HC_HCT164_3
Modifications:		f this data sheet has been NXP Semiconductors.	redesigned to comply	with the new identity
	<ul> <li>Legal texts h</li> </ul>	ave been adapted to the ne	ew company name w	here appropriate.
	<ul> <li>Added type r</li> </ul>	number 74HC164BQ (DHV	QFN14 / SOT762-1 p	ackage).
	<ul> <li>For type num SOT108-1.</li> </ul>	nbers 74HC164D and 74H0	CT164D: sot number	SOT108-2 changed to
74HC_HCT164_3	20050404	Product data sheet	-	74HC_HCT164_ CNV_2
74HC_HCT164_CNV_2	19901201	Product specification	-	-

# 14. Legal information

### 14.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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